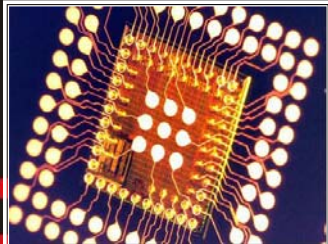


*New Embedded Package Technology
using Large-Scale Panel Assembly (FO-WLP)*

J DEVICES

*J-DEVICES CORPORATION
Packaging Research & Development Center
Akio Katsumata*



About J-DEVICES

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About J-DEVICES

Foundation

- Established with capital from NAKAYA Micro Devices, Amkor and Toshiba in 2009.
- Merged Fujitsu Semiconductor's assembly and test division (FIM) in 2012.
- Will merge Renesas three assembly and test factories in 2013.

Goal

- To become one of the leading global companies in the semiconductor backend business.

Focus

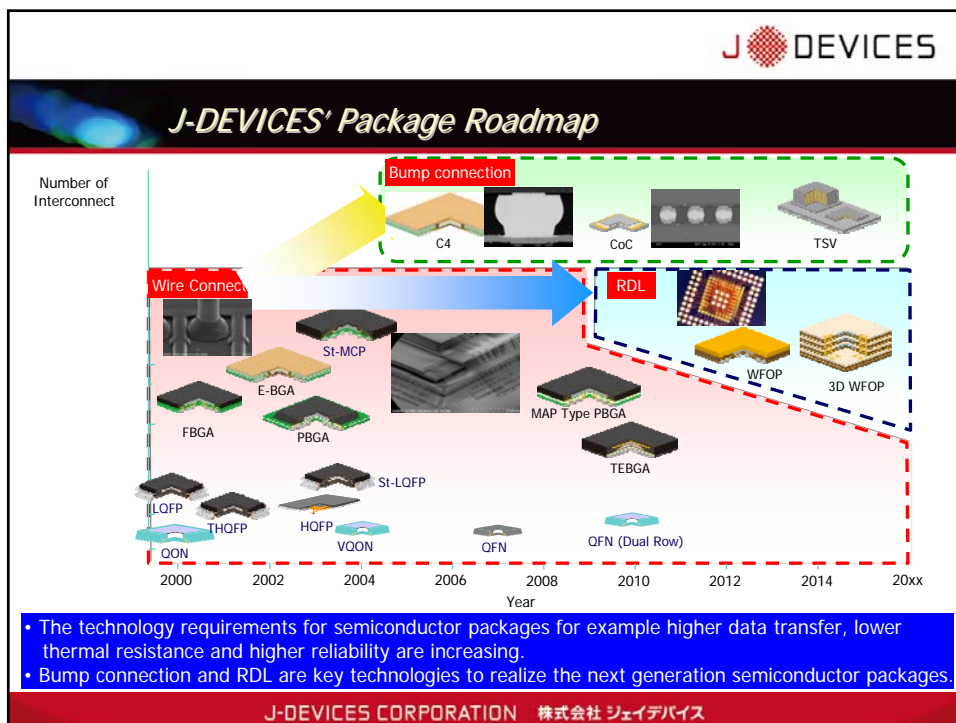
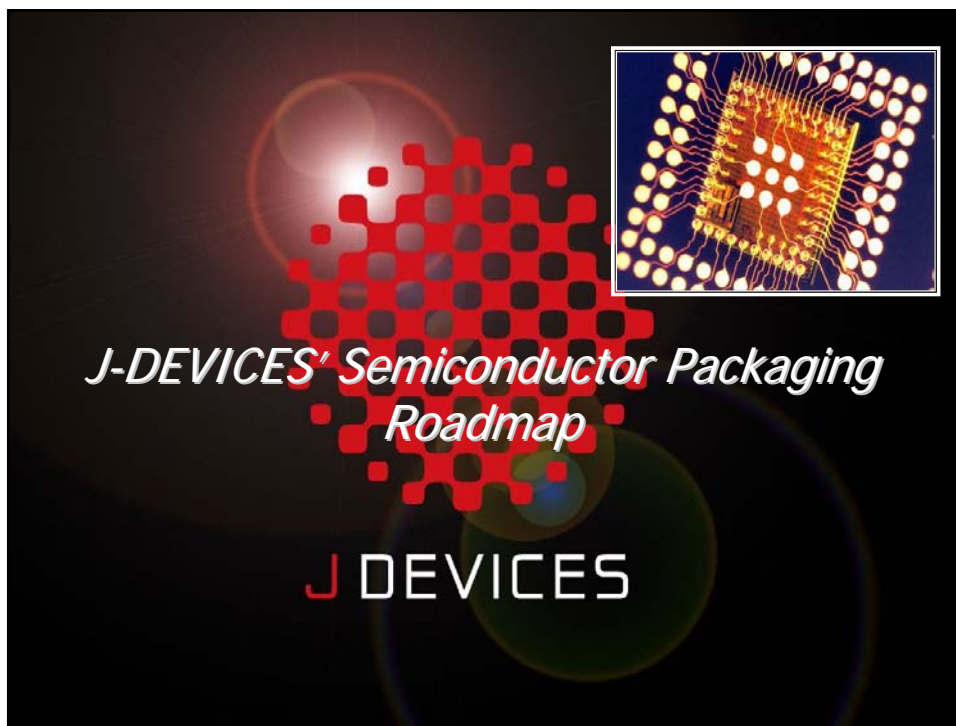
- R&D is focused on developing new connecting technologies and has the experience to manufacture using new connecting technologies.
 - ex. Three years experience with 40um bump pitch CoC manufacturing.
- Automotive product experience

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- 2. FO-WLP Market Trend & J-DEVICES' Development Concept*
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- 5. Target Applications & Roadmap*
- 6. Conclusion*







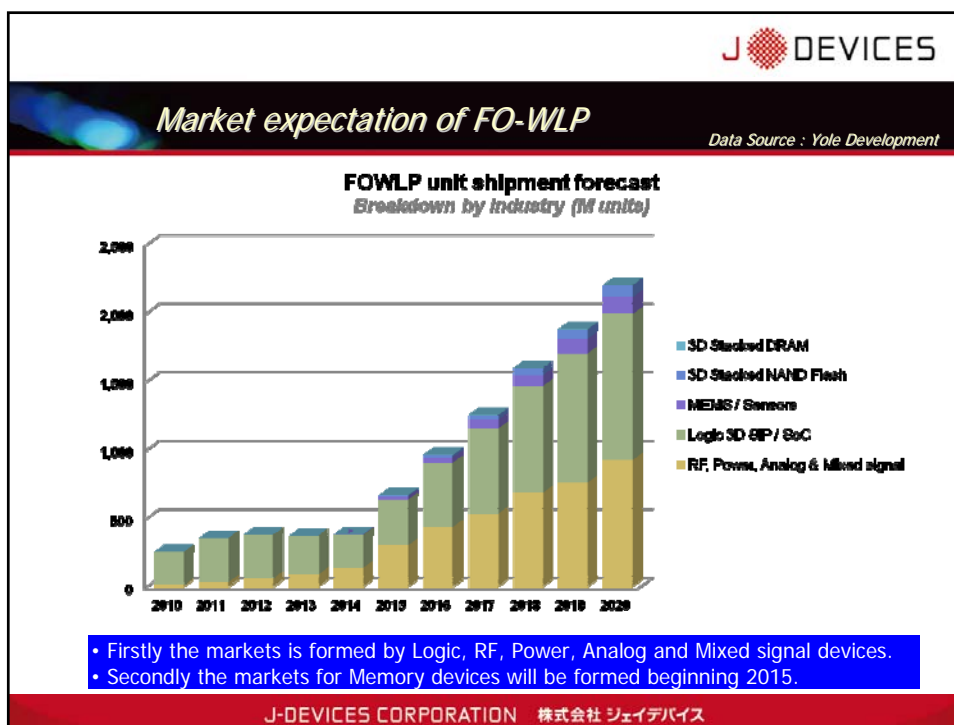
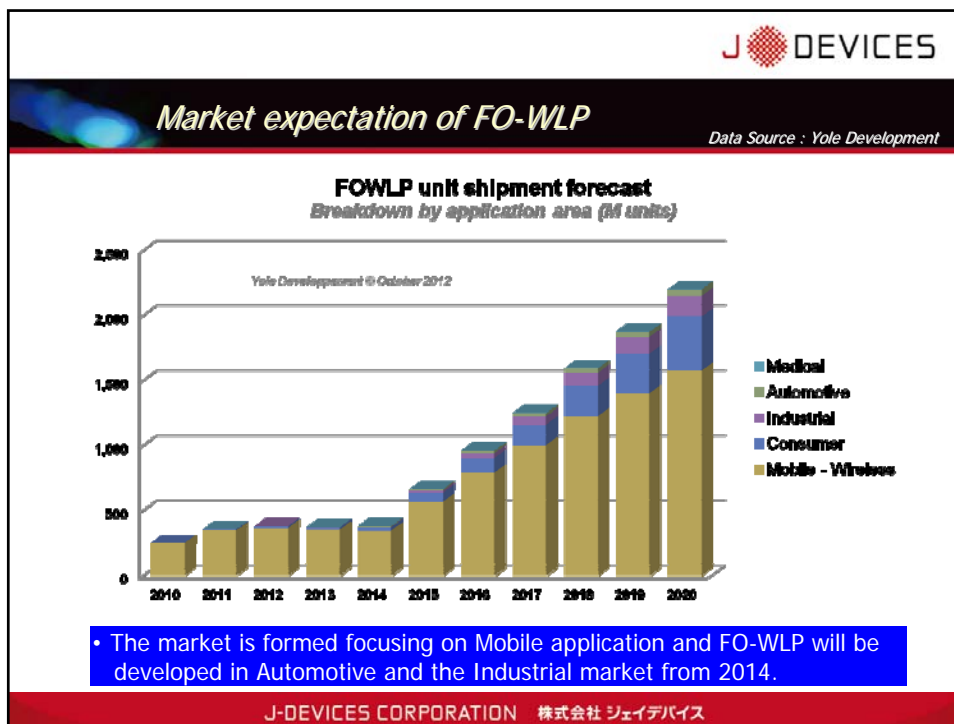
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Validity of FO-WLP Technology

- ✓ Package design of FO-WLP is INDEPENDENT from chip size
→ Fan-In WLPs are chip size package. All balls must fit UNDER chip shadow.
- ✓ Large panel assembly
→ Larger throughput
- ✓ Design flexibility
→ Redistribution layer easily forms 2D & 3D design.
- ✓ Suitable for low package profile demand
→ No need for wire bonding height and substrate thickness.

The pin unit price of a package falls drastically with enlargement of the panel size.

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J-DEVICES' FO-WLP Development Concept

Higher density RDL
L/S = 20/20(um) is achievable

3D Packaging capability
Die stack structure is achievable

Connect to Finer Pad Pitch
50um Pad Pitch is achievable

Better EMI Shielding effect

Better thermal performance than molded BGA

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J-DEVICES' WFOP Technology

Top view of chip area
(Line width: 20 um)

Pad interconnection

SEM image

Panel appearance

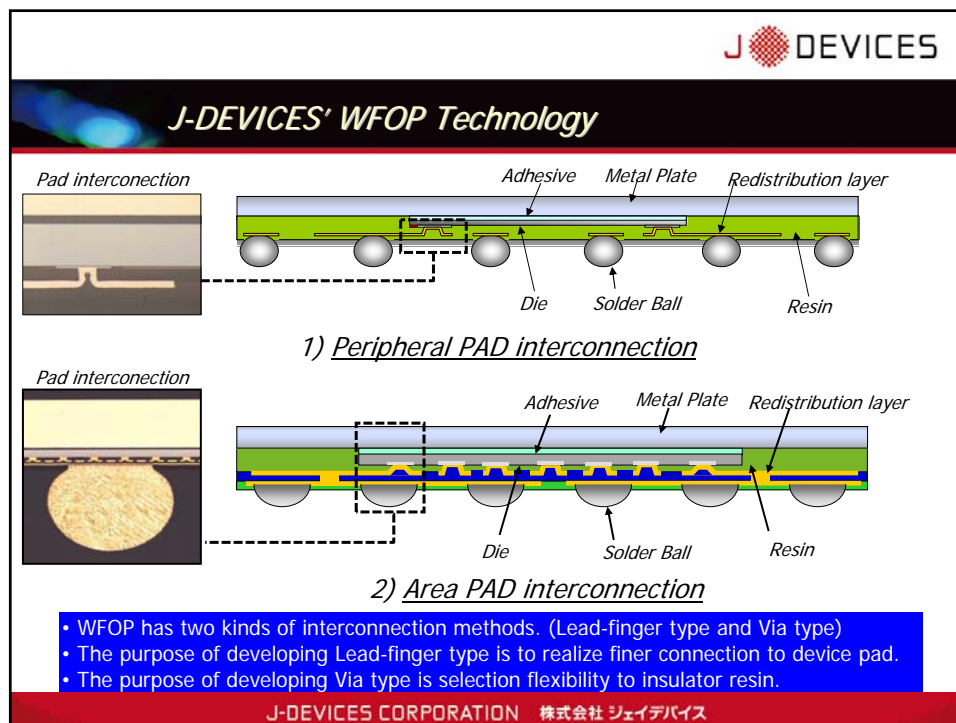
Backside view

Redistribution layer
Metal Base Plate
Resin
Die
Adhesive
Solder Ball

J-DEVICES' Advantage

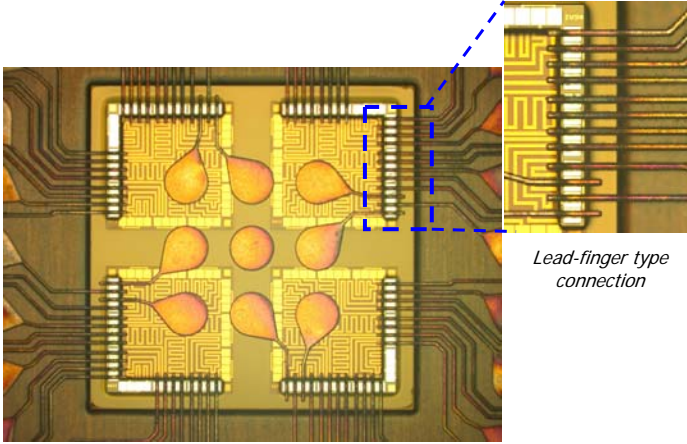
- RDL is directly connected to the pad.
- RDL technology is based on PCB technology which makes it cost-competitive.
- Manufacturing work uses large panel.
- 50um pad pitch interconnection technology is already developed.

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WFOP : Redistribution layer for 50um-pitch pads



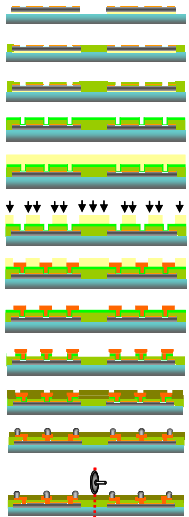
Lead-finger type connection

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Process Flow

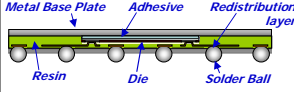
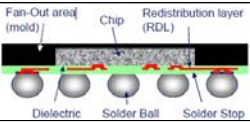
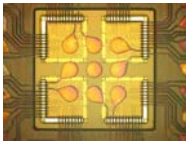
- Die attach to metal plate
- Embedded dies by insulator resin
- Via formation
- Seed layer formation (Ti/Cu)
- Photo-resist coating for Copper wiring
- Exposure and / Development
- Copper plating
- Resist removing
- Seed layer etching
- Insulating layer formation
- Solder ball mounting
- Singulation




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Comparison table of WFOP and eWLB

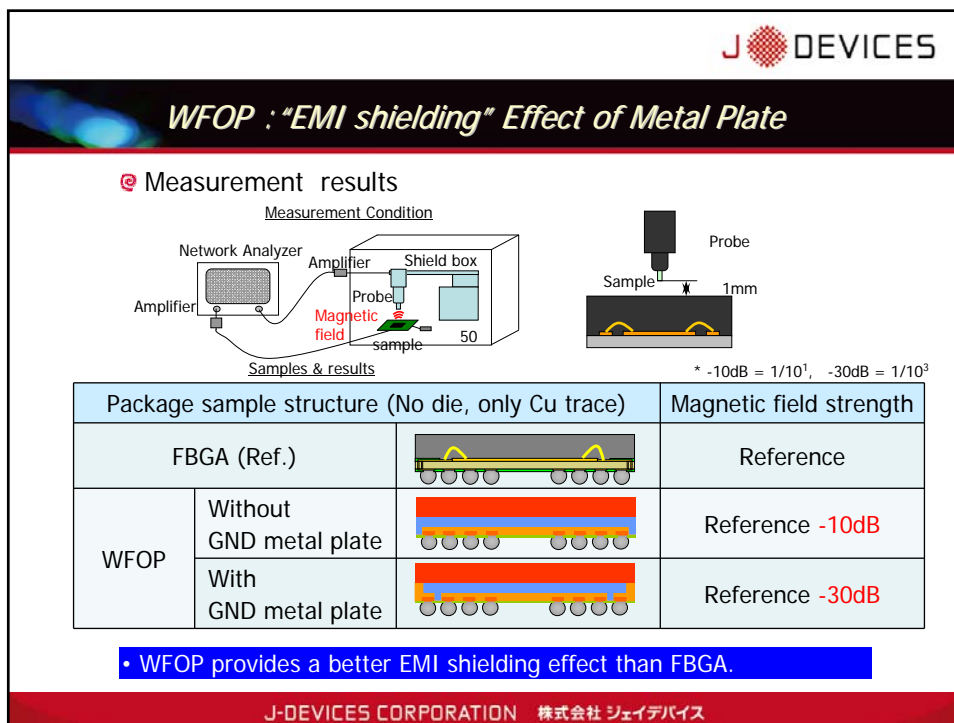
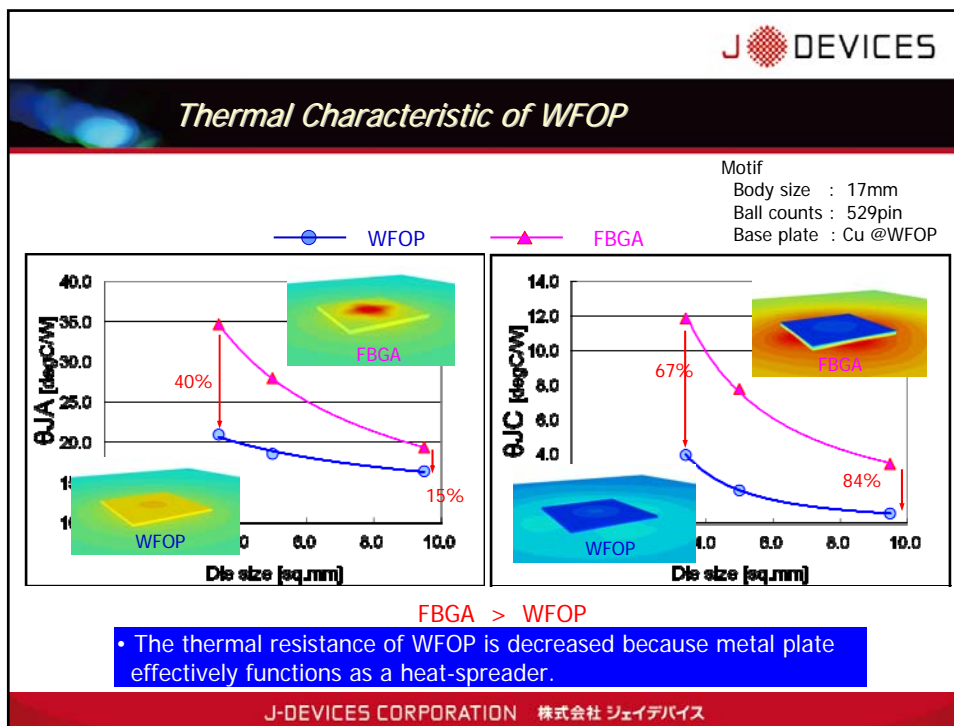
	WFOP™	eWLB
Package structure		
RDL (Redistribution Line) formation technology	PCB semi-additive technology Cost competitive	Semiconductor photolithography
Manufacturing work size	Panel (Large Size) Cost competitive	Wafer(200mm /300mm)
Minimum device pad pitch	50um 	70um Influence of die shift problem caused by mold resin shrinkage

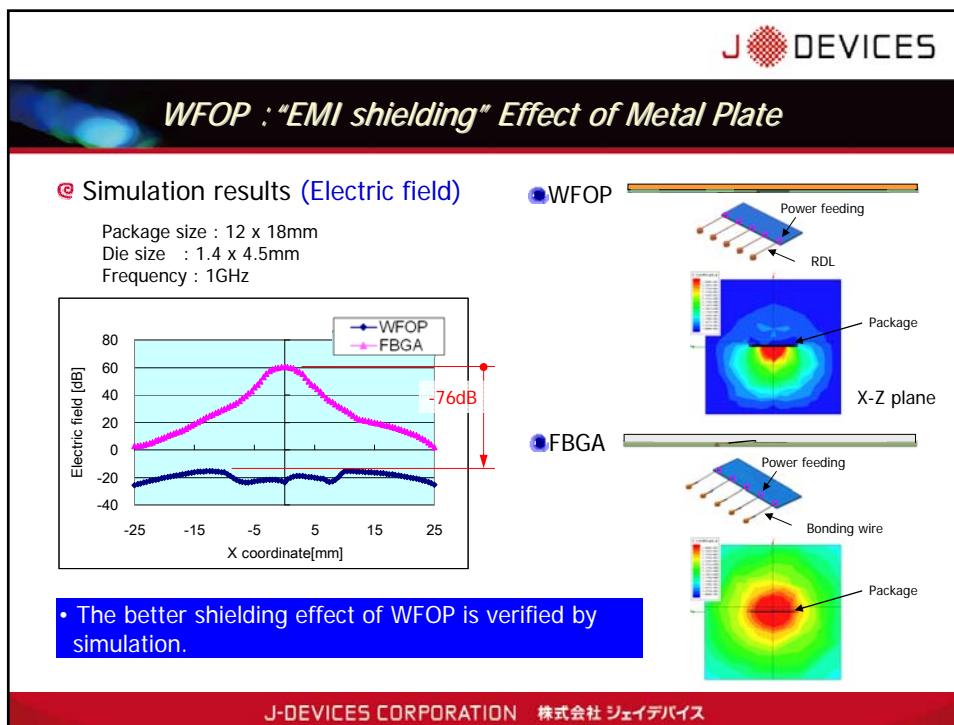
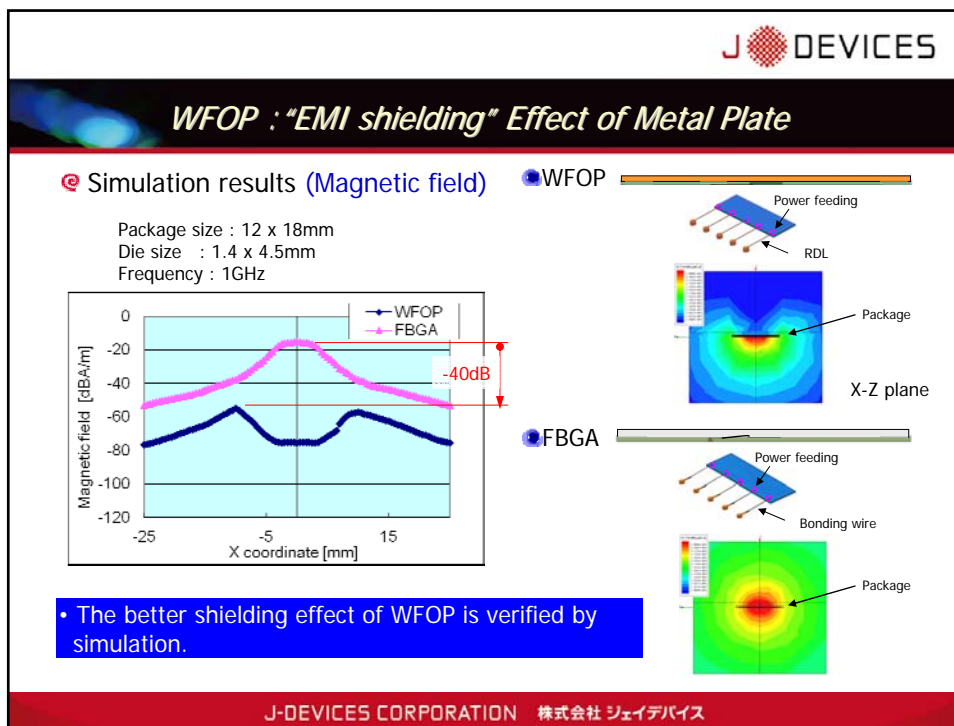
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WFOP Characteristics & Reliability

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Solder Joint Reliability

Ⓢ Warpage problem of current BGA Package

- Warpage direction is different because of environment temperature.
- Shape of solder joint is affected by warpage.

To get higher solder joint reliability, it is necessary to reduce the warpage caused by the environment temperature change.

The relationship between environment temperature and package warpage

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Solder Joint Reliability

Ⓢ Advantage of WFOP

- 1) The package warpage caused by the environment temperature change is small because the metal plate has high elasticity.
- 2) C.T.E of the metal plate is adjustable to that of the mother board.

➔ WFOP achieves improved solder joint reliability by optimizing the material property of metal plate.

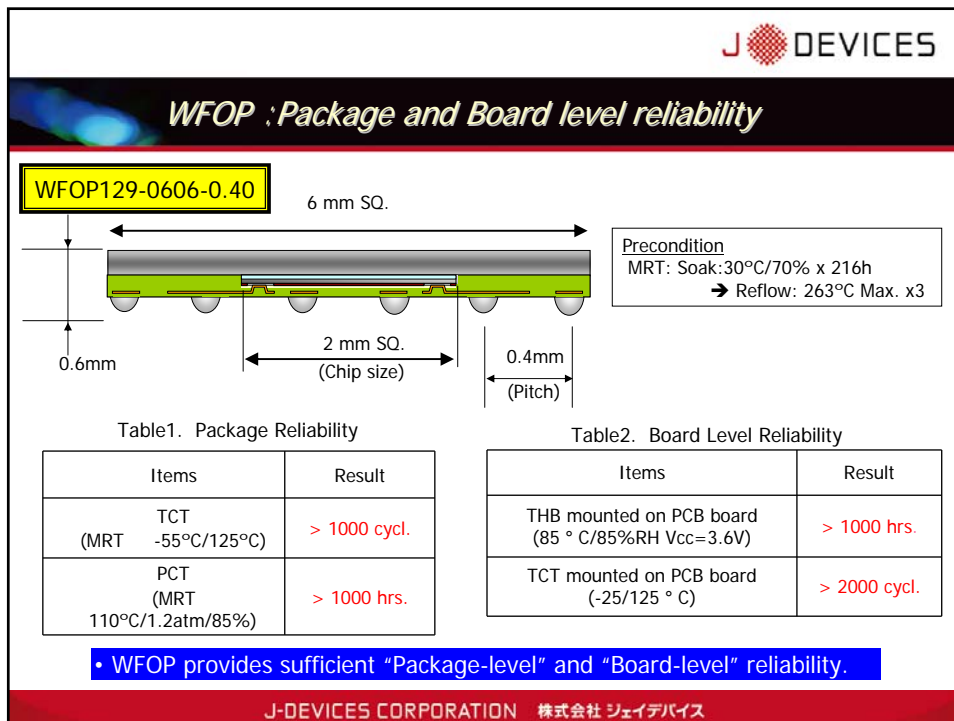
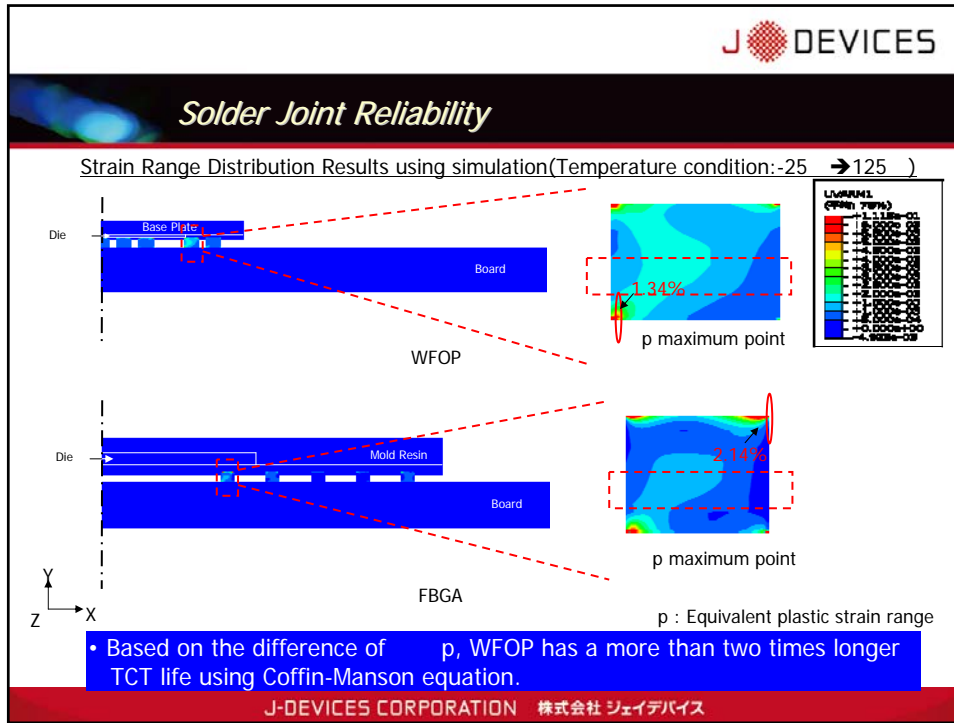
Warpage Variation on TCT Condition (125 -25)

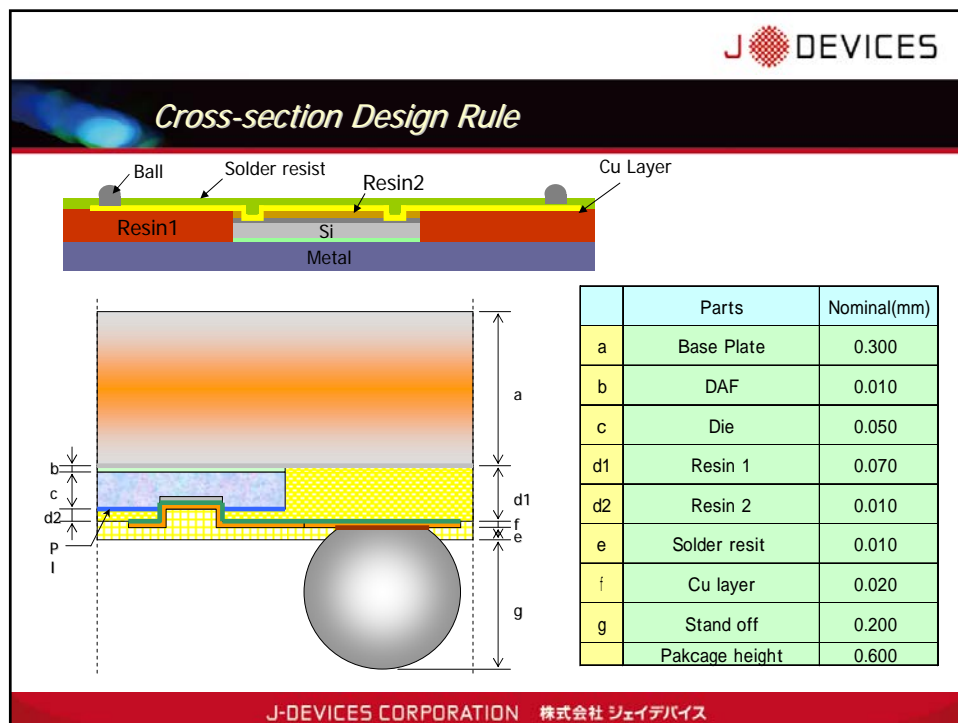
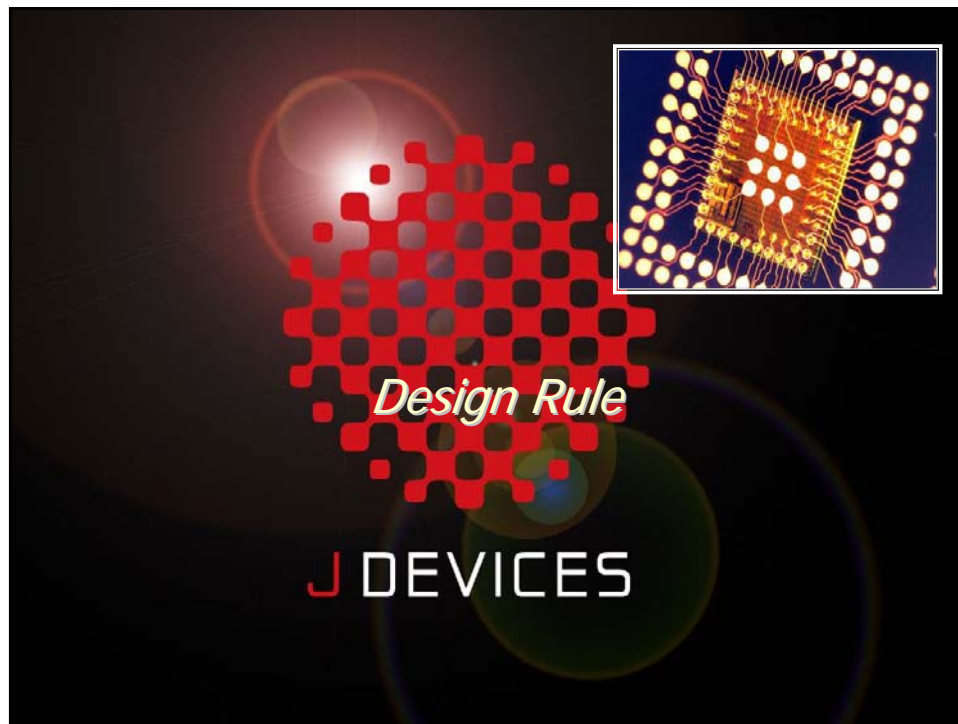
Deformed Shape at -25 (Corner Ball)

Temp.	FBGA	WFOP
125		
-25		

*Comparison with original shape

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Design Rule to connect Peripheral Pad

Current Design Rule	Next generation
50um pitch	45um pitch
<p>Die Die pad Pad opening (opening collectively) L1 Copper pattern L/S = 20um/ 20um Via land [80um dia.] (adjacent solder ball)</p>	<p>Die Die pad Pad opening (opening collectively) L1 Copper pattern L/S 15um/ 15um^{*1} 18um/ 18um^{*2} Via land [70um^{*1}/ 65um^{*2} dia.] (adjacent solder ball)</p> <p>^{*1}:option-1 ,^{*2}:option-2</p>

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Design Rule to connect Area Pad

Zoom

Die
Die pad
Pad opening (opening separately)
L1 Cu pattern
Via land (adjacent solder ball)

Symbol	Item	Design value		
		Current	Next generation Option-1	Option-2
	Line width	20um	15um	18um
	Line space	20um	15um	18um
C	Die pad opening diameter	50um	40um	40um
D	Via land diameter	80um	70um	65um
E	Via land diameter	80um	70um	65um
F	Via diameter	50um	40um	40um
G	Via land - line space	20um	15um	18um
H	Via pitch	100um	85um	83um
I	Ball land diameter	Refer other page		
J	Ball land - line space	20um	15um	18um
K	Ball land - via land space (Same NET)	0um		
K'	Ball land - via land space (Different NET)	20um	15um	18um

Pad connect (Area pad)

Via (Interlayer connect)

Ball land

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J-DEVICES' WFOP Package Structure

Application	RF	System LSI	Memory
Replace Package	 FBGA	 FC-BGA	 MCP
WFOP Structure			
Advantage	EMI shielding effect Better Electrical performance Reduce Thermal resistance	Thinner Better Electrical performance	Multi-Channel Reduce Thermal Resistance

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High Performance FCBGA

	RDL 2layers	RDL 3layers
Package Total Height	935um	965um

Material	Thickness (Height)
Metal base plate	300um
Ball Stand-off (1mm pitch)	500um
Die	50um
Cu wiring	12um
Interlayer insulator	18um

- No need for bump and package substrate.
- Like core-less substrate structure. Reduced capacitance and inductance of wiring.

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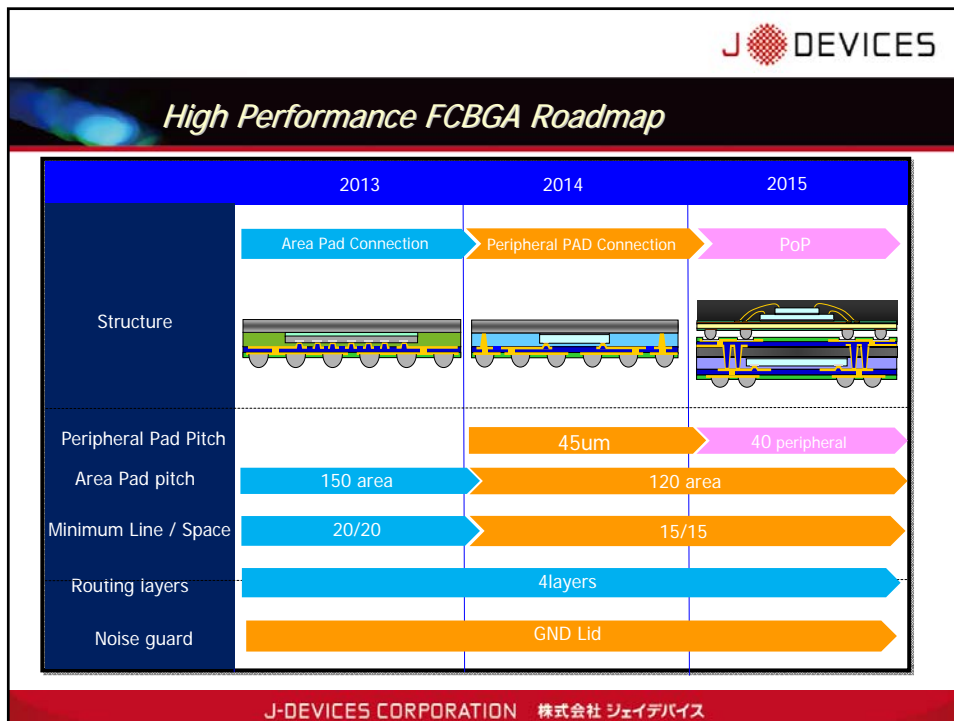
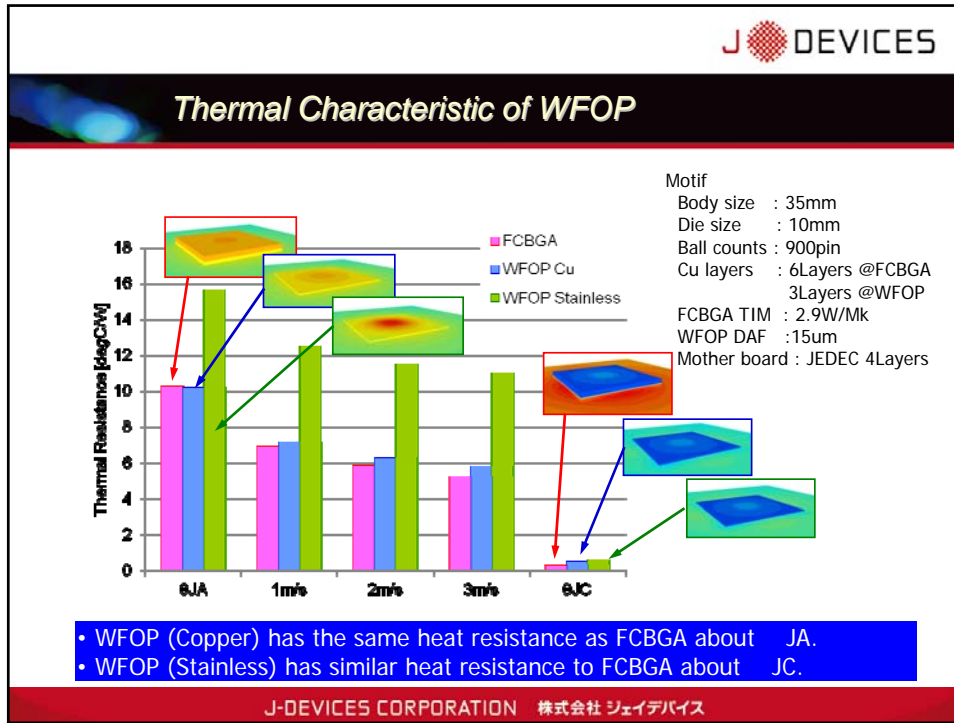
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High Performance FCBGA

WFOP

FC-BGA

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High Performance Flash Memory Module

Package Total Height	RDL 3layers 1055um
----------------------	-----------------------

Material	Thickness (Height)
Metal base plate	300um
Ball Stand-off (1.0mm pitch)	320um
Die	50um
Cu wiring	12um
Interlayer insulator	15um

- Enables "Die stack module" without TSV structure.
- Enables higher multi-channel memory module without custom memory devices.
- Lower Thermal Resistance and high EMI shielding performance.


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High Performance Flash Memory Module Roadmap

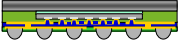
	2013	2014	2015
Number of Channels	4 Channels	8 Channels	16 Channels
Structure			
Number of Dies	4 dies / PKG	8 dies / PKG	16 dies / PKG
Total thickness	1.2mm / 4dies stack	1.2mm / 8 dies stack	1.0 mm / 8 dies stack
Die thickness	50um	40um	25um
Pad pitch	150um	120um	120um
Min Line / Space	40/40	20/20	20/20

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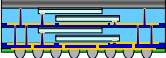
Internal Reliability Test Plan

FC-BGA Type.




Item	Condition
MSL (Pre-conditioning)	Soak:30C/70%RH/216H Reflow:260C, 3times
PCT (with Pre-conditioning)	110C/1.2atm/85%/500H
TCT (with Pre-conditioning)	-55C/125C/500cycles
HTS	150C/1000H
THB (with Pre-conditioning)	Pre-conditioning 85C/85%RH/5.5V/1000H

Memory Type.



Item	Condition
MSL (Pre-conditioning)	Soak:30C/70%RH/192H Reflow:260C, 4times
PCT (with Pre-conditioning)	110C/1.2atm/85%/500H
TCT (with Pre-conditioning)	-55C/125C/1000cycles
HTS	150C/1000H
HAST (with Pre-conditioning)	110C/85%/3.6V/300H
THB	85C/85%RH/3.6V/1000H
Board level TCT	TBD
Drop test	TBD

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Conclusion

- The technology requirements for semiconductor packages for example higher data transfer, lower thermal resistance and higher reliability are increasing. Bump connection and RDL are key technologies to realize next generation packages.
- Panel scale assembly is a new solution to change the packaging manufacture style. (from One by One to Batch Processing)
- The development concept of WFOP is connect to finer pad pitch, thermal performance, EMI shielding and 3D packaging capability.
- Internal reliability test will be finished by end of April using the high performance FCBGA and high performance flash memory module structure.

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